# **SKT 1000**



## **Capsule Thyristor**

### Line Thyristor

#### **SKT 1000**

#### **Features**

- Hermetic metal case with ceramic insulator
- Capsule package for double sided cooling
- · International standard case
- Off-state and reverse voltages up to 2800 V
- · Amplifying gate

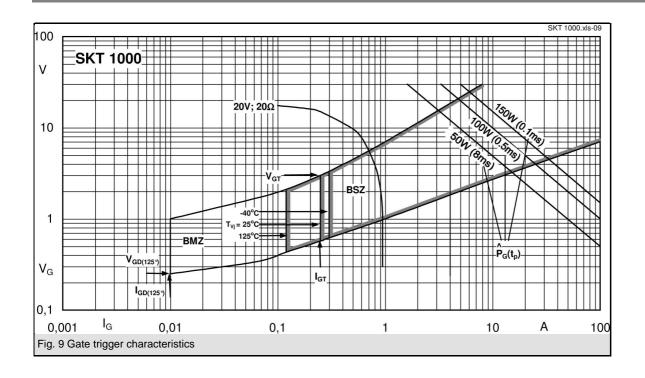
#### **Typical Applications**

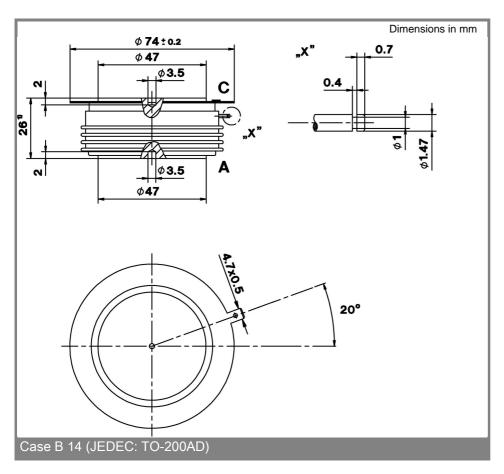
- DC motor control (e. g. for machine tools)
- Controlled rectifiers(e. g. for battery charging)
- AC controllers
  - (e. g. for temperature control)
- Recommended snubber network e. g. for  $V_{VRMS} \le 400 \text{ V}$ : R = 33  $\Omega/32$  W, C = 1  $\mu\text{F}$

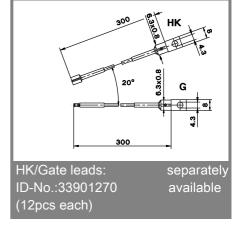
$V_{RSM}$	V <sub>RRM</sub> , V <sub>DRM</sub>	I <sub>TRMS</sub> = 2300 A (maximum value for continuous operation)		
V	V	I <sub>TAV</sub> = 1000 A (sin. 180; DSC; T <sub>c</sub> = 85 °C)		
1300	1200	SKT 1000/12E		
1700	1600	SKT 1000/16E		
2300	2200	SKT 1000/22EL2		
2700	2600	SKT 1000/26EL2		
2900	2800	SKT 1000/28EL2		

Symbol	Conditions	Values	Units
I <sub>TAV</sub>	sin. 180; T <sub>c</sub> = 100 (85) °C;	710 (1000 )	Α
$I_D$	2 x P8/180; T <sub>a</sub> = 45 °C; B2 / B6	360 / 500	Α
	2 x P8/180F; T <sub>a</sub> = 35 °C; B2 / B6	1250 /1750	Α
I <sub>RMS</sub>	2 x P8/180; T <sub>a</sub> = 45 °C; W1C	400	Α
I <sub>TSM</sub>	T <sub>vj</sub> = 25 °C; 10 ms	19000	Α
	$T_{vj}$ = 125 °C; 10 ms	16500	Α
i²t	T <sub>vj</sub> = 25 °C; 8,3 10 ms	1800000	A²s
	T <sub>vj</sub> = 125 °C; 8,3 10 ms	1360000	A²s
$V_{T}$	T <sub>vj</sub> = 25 °C; I <sub>T</sub> = 3600 A	max. 2	V
$V_{T(TO)}$	$T_{vj} = 125  ^{\circ}\text{C}$	max. 1,14	V
r <sub>T</sub>	$T_{vj} = 125  ^{\circ}\text{C}$	max. 0,243	mΩ
$I_{DD}; I_{RD}$	$T_{vj}$ = 125 °C; $V_{RD}$ = $V_{RRM}$ ; $V_{DD}$ = $V_{DRM}$	max. 160	mA
t <sub>gd</sub>	$T_{vj} = 25 \text{ °C; } I_G = 1 \text{ A; } di_G/dt = 1 \text{ A/}\mu\text{s}$	1	μs
t <sub>gr</sub>	$V_{\rm D} = 0.67 * V_{\rm DRM}$	2	μs
(di/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C	max. 125	A/µs
(dv/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C	max. 1000	V/µs
t <sub>q</sub>	$T_{vj} = 125 ^{\circ}\text{C}$ ,	100 250	μs
I <sub>H</sub>	$T_{vj} = 25 ^{\circ}\text{C}$ ; typ. / max.	250 / 500	mA
IL	$T_{vj}$ = 25 °C; $R_G$ = 33 $\Omega$ ; typ. / max.	500 / 2000	mA
V <sub>GT</sub>	$T_{vj}$ = 25 °C; d.c.	min. 3	V
I <sub>GT</sub>	$T_{vj} = 25 ^{\circ}\text{C}; \text{d.c.}$	min. 250	mA
$V_{GD}$	$T_{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	max. 0,25	V
$I_{GD}$	$T_{vj}$ = 125 °C; d.c.	max. 10	mA
R <sub>th(j-c)</sub>	cont.; DSC	0,021	K/W
$R_{th(j-c)}$	sin. 180; DSC / SSC	0,0225 / 0,054	K/W
R <sub>th(j-c)</sub>	rec. 120; DSC / SSC	0,027 / 0,06	K/W
R <sub>th(c-s)</sub>	DSC / SSC	0,005 / 0,01	K/W
$T_{vj}$		- 40 <b>+</b> 125	°C
T <sub>stg</sub>		- 40 + 130	°C
V <sub>isol</sub>		-	V~
-	mounting force	22 25	kN
а			m/s²
m	approx.	480	g
Case		B 14	









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